L Number	Hits	Search Text	DB	Time stamp
17	7657	"alignment mark" or (alignment adj mark)	USPAT; EPO; JPO; IBM_TDB	2003/06/03 09:28
21	21294	"chemical mechanical polishing" or CMP	USPAT; EPO; JPO; IBM_TDB	2003/06/03 04:30
22	33	(("magnetoresistive random access memory" or MRAM) and (("silicon oxide" or SiO or dielectric or insulating) and (copper or Cu) and (channels or vias or trench or openings))) and ("chemical mechanical polishing" or CMP)	USPAT; EPO; JPO; IBM_TDB	2003/06/03 04:30
20	113	("magnetoresistive random access memory" or MRAM) and (("silicon oxide" or SiO or dielectric or insulating) and (copper or Cu) and (channels or vias or trench or openings))	USPAT; EPO; JPO; IBM_TDB	2003/06/03 1:21
31	112	(dielectric or insulating) and (copper or Cu) and (channels or vias or trench or openings) and ("magnetoresistive random access memory" or MRAM)	USPAT; EPO; JPO; IBM_TDB	2003/06/03 11:33
16	568	"magnetoresistive random access memory" or MRAM	USPAT; EPO; JPO; IBM_TDB	2003/06/03 1:33
34	511	("alignment mark" or (alignment adj mark)) and (copper or Cu) and (channels or vias or trench or openings)	USPAT; EPO; JPO; IBM_TDB	2003/06/03 10:34
35	144	("magnetoresistive random access memory" or MRAM) and (copper or Cu) and (channels or vias or trench or openings)	USPAT; EPO; JPO; IBM_TDB	2003/06/03 1:34
19	68271	("silicon oxide" or SiO or dielectric or insulating) and (copper or Cu) and (channels or vias or trench or openings)	USPAT; EPO; JPO; IBM_TDB	2003/06/03 1:51
36	4445	("chemical mechanical polishing" or CMP) and (("silicon oxide" or SiO or dielectric or insulating) and (copper or Cu) and (channels or vias or trench or openings)) and etch$3	USPAT; EPO; JPO; IBM_TDB	2003/06/03 10:53
37	4798	("chemical mechanical polishing" or CMP) and (("silicon oxide" or SiO or dielectric or insulating) and (copper or Cu) and (channels or vias or trench or openings))	USPAT; EPO; JPO; IBM_TDB	2003/06/03 10:55
38	378	("magnetoresistive random access memory" or MRAM) and (channels or openings or windows or trench or vias or contact)	USPAT; EPO; JPO; IBM_TDB	2003/06/03 10:57
39	46	(("magnetoresistive random access memory" or MRAM) and (channels or openings or windows or trench or vias or contact)) and 43$/c.cls.	USPAT; EPO; JPO; IBM_TDB	2003/06/03 10:57